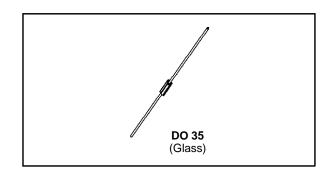


SMALL SIGNAL SCHOTTKY DIODE



General purpose metal to silicon diode featuring very low turn-on voltage and fast switching.

This device has integrated protection against excessive voltage such as electrostatic discharges.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit	
V_{RRM}	Repetitive Peak Reverse Voltage	100	V	
l _F	Forward Continuous Current*	T _a = 25 °C	100	mA
I _{FRM}	Repetitive Peak Forward Current*	$\begin{array}{l} t_p \leq 1s \\ \delta \leq 0.5 \end{array}$	350	mA
I _{FSM}	Surge non Repetitive Forward Current*	$t_p \le 10ms$	750	mA
P _{tot}	Power Dissipation*	100	mW	
$T_{stg} \ T_{j}$	Storage and Junction Temperature Range	- 65 to +150 - 65 to +125	°C	
TL	Maximum Lead Temperature for Soldering during 10s at 4mm from Case 230			

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
$R_{th(j-a)}$	Junction-ambient*	300	°C/W

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol		Min.	Тур.	Max.	Unit		
V_{BR}	T _j = 25°C	$I_R = 100 \mu A$		100			V
V _F * *	T _j = 25°C	I _F = 1mA			0.4	0.45	V
	T _j = 25°C	I _F = 200mA				1	
I _R * *	T _j = 25°C		V _R = 50V			0.1	μΑ
	T _i = 100°C					20	

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Тур.	Max.	Unit
С	T _i = 25°C	$V_R = 1V$	f = 1MHz		2		pF

^{*} On infinite heatsink with 4mm lead length * * Pulse test: $t_p \leq 300 \mu s~\delta < 2 \%$

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Figure 1. Forward current versus forward voltage at different temperatures (typical values).

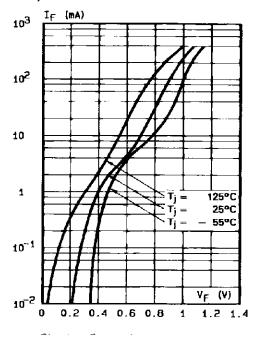


Figure 2. Forward current versus forward voltage (typical values).

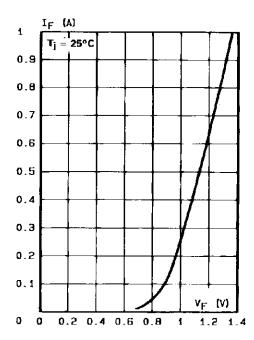


Figure 3. Reverse current versus junction temperature.

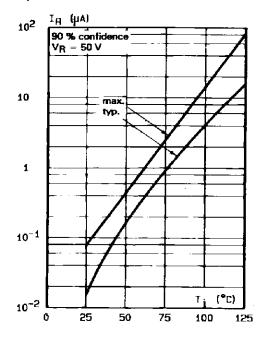


Figure 4. Reverse current versus continuous reverse voltage (typical values).

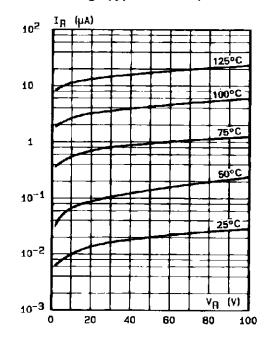
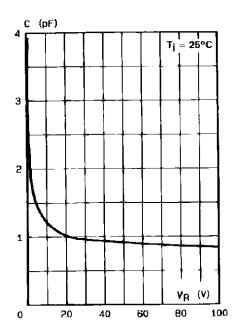
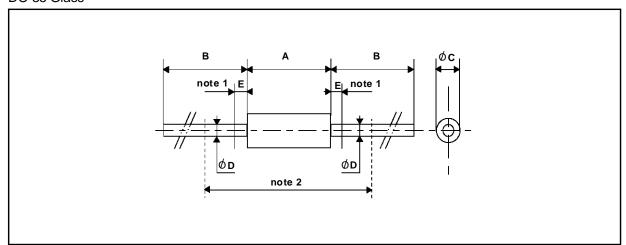


Figure 5. Capacitance C versus reverse applied voltage $V_{\mbox{\scriptsize R}}$ (typical values).



PACKAGE MECHANICAL DATA

DO 35 Glass



	REF. Millimeters Inches				
REF.			hes	NOTES	
	Min.	Max.	Min.	Max.	
Α	3.050	4.500	0.120	0.117	
В	12.7		0.500		1 - The lead diameter Ø D is not controlled over zone E
ØC	1.530	2.000	0.060	0.079	2 - The minimum axial lengh within which the device may be placed
ØD	0.458	0.558	0.018	0.022	with its leads bent at right angles is 0.59"(15 mm)
Е		1.27		0.050	

Cooling method: by convection and conduction Marking: clear, ring at cathode end.

Weight: 0.15g

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